

明新科技大學 98 學年度研究所招生考試 試題卷

系所名稱	類別	科目	節次	准考證號碼 (考生請填入)	考試日期
電機工程研究所 (電機組)	碩士班	電子學	第二節		98/5/3

※答案須寫在答案卷內，否則不予計分。

1. According to Fig. 1, assume that the operational amplifier is ideal and  $R_2/R_1=R_4/R_3$ . Prove that  $v_o=(R_2/R_1)(v_2-v_1)$ . (10%)

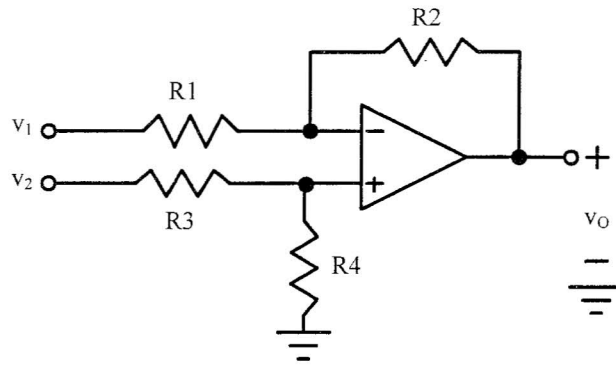


Fig. 1

2. Consider the circuit configuration shown in Fig. 2. Assume that the operational amplifier is ideal. Derive the voltage gain  $A_v=v_o/v_i$ . (10%)

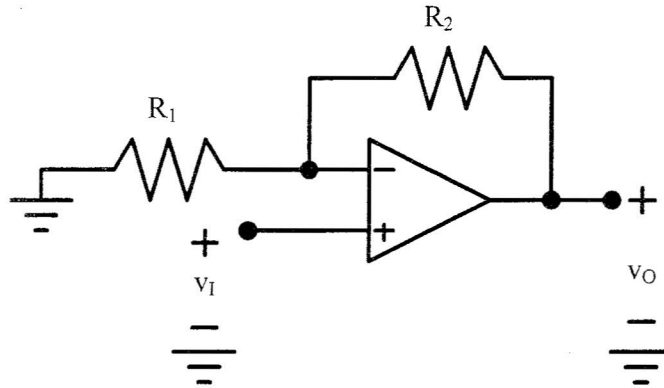


Fig. 2

3. Determine the current  $I_D$  and the diode voltage  $V_D$  for the circuit shown in Fig. 3 with  $V_{DD}=5V$  and  $R=1k\Omega$ . Assume that the diode piecewise-linear model parameters are  $V_{D0}=0.65V$  and  $r_D=20\Omega$ . (10%)

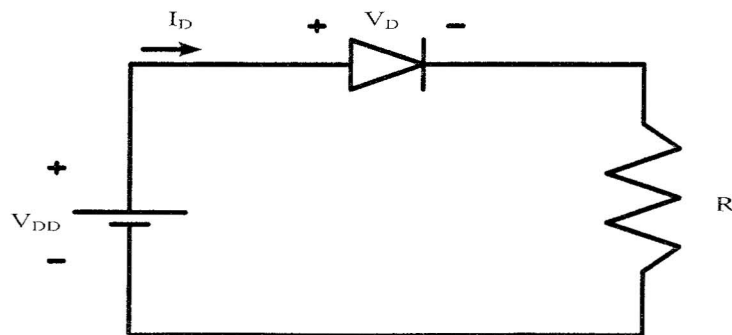


Fig. 3

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4. For the current mirror circuit in Fig. 4 with  $V_{CC}=V_{EE}=10V$ , assume that the forward voltage drop of  $V_{BE}=0.7V$ . Find the required value of  $R$  to implement the constant current source  $I_{REF}=1mA$ . (10%)

5. Analyze the circuit of Fig. 5 to determine  $I_C$  and  $V_C$ . Assume that  $\beta=100$ . (10%)

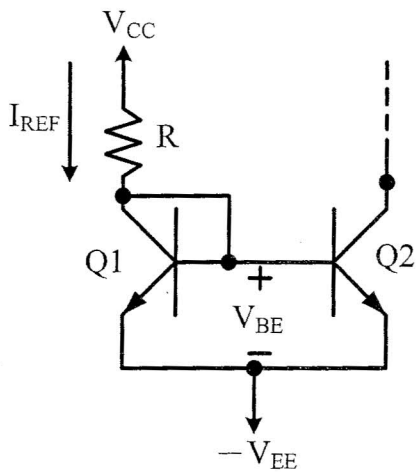


Fig. 4

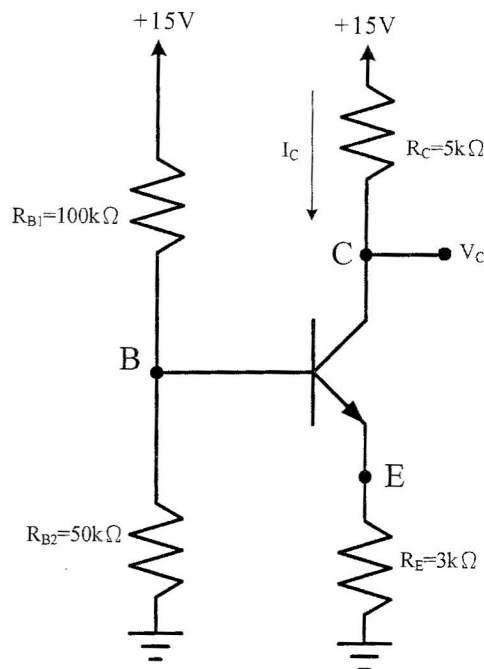
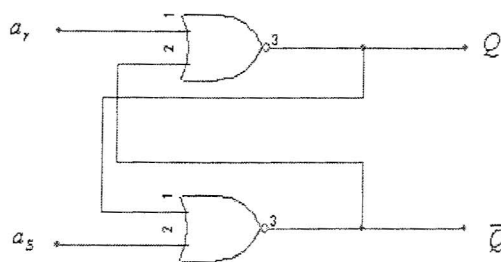


Fig. 5

6. Find the truth table in Fig. 6. (10%)



$a_7$	$a_5$	$Q_{n+1}$	$\overline{Q}_{n+1}$
0	0		
0	1		
1	0		
1	1		

Fig. 6

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7. Find the time constant of the circuit shown in Fig. 7. (10%)

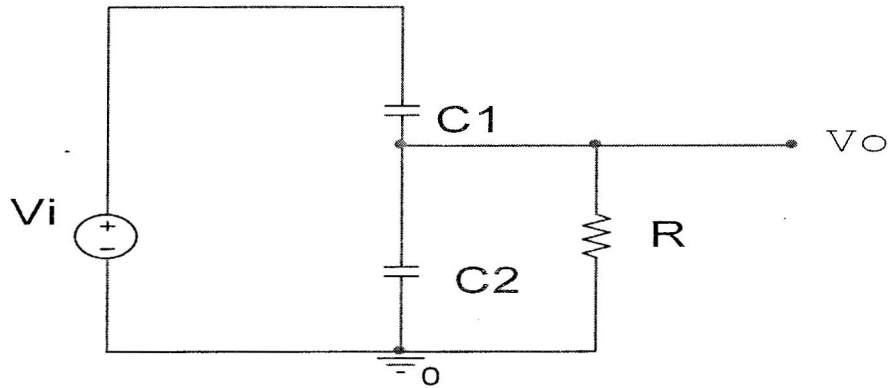


Fig. 7

8. Find the value required for  $R$ , and find the dc voltage  $V_D$  in Fig. 8 where

$$I_D = 80 \mu A$$

$$V_t = 0.6v \quad \mu_n C_{ox} = 200 \mu A/V^2 \quad L = 0.8 \mu m \quad \text{and} \quad W = 4 \mu m.$$

Neglect the channel-length modulation effect. (10%)

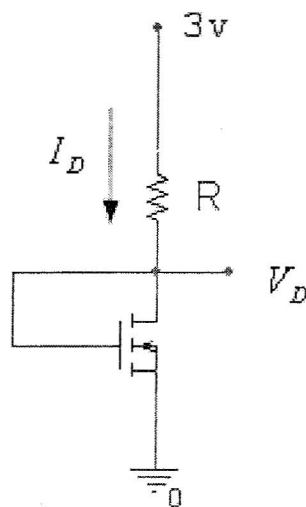


Fig. 8

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9. Find  $R_D$  and  $R_S$  in Fig. 9. The transistor operates at  $I_D = 0.4mA$  and  $V_D = +0.5v$  with

$$V_t = 0.7V, \mu_n C_{ox} = 100\mu A/V^2, L = 1\mu m, \text{ and } W = 32\mu m.$$

Neglect the channel-length modulation effect. (10%)

10. Plot high-frequency equivalent circuit model for the MOSFET shown in Fig. 10. (10%)

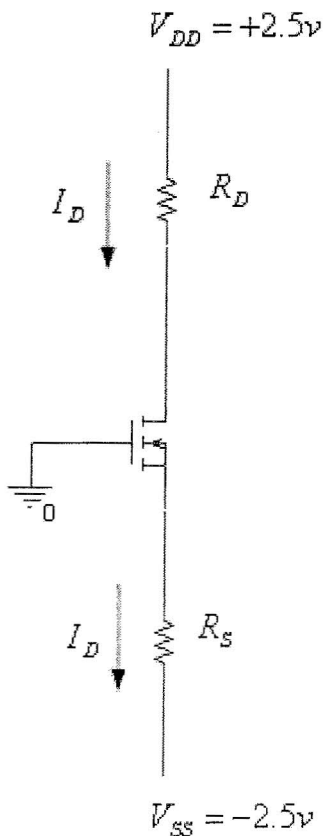


Fig. 9

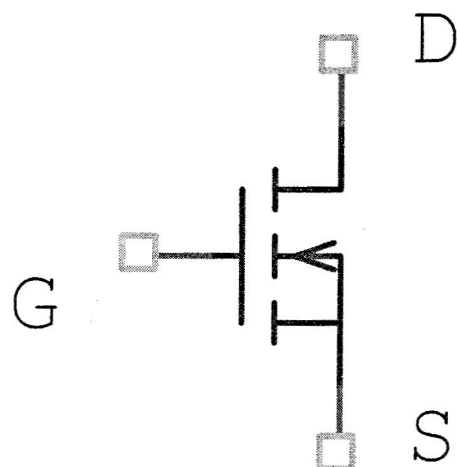


Fig. 10